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**Microstructure, electrical properties and application of
bismuth titanate ceramics and glass-ceramics for low-
energy electronic devices**

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Aurivillius family oxides including $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ are of great interest in the last years due to their potential for:

- applications as transducers, capacitors, and acoustic piezo-sensors with high temperature piezoelectric properties;**
- ferroelectrics with high Curie temperature;**
- high temperature glasses with various refractive index;**
- electro-optical modulators and deflectors for lasers and high power light beams;**
- glasses with various polarization, based on diffusion of titanium layers;**
- cascade piezoelectric devices up to 3 kW/kg and 20% thermo effectivity;**



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**Applications of bismuth-based ferroelectrics are strongly influenced by the method of preparation.
Different methods of synthesis leads to the generation of different microstructures and specific electrical properties.**



Purpose

The purpose of the present work is the preparation of composite materials in the system $\text{Bi}_2\text{O}_3\text{-TiO}_2\text{-SiO}_2\text{-Nd}_2\text{O}_3$ obtained by melt quenching method and the study of their electrical properties depending on composition and temperature.



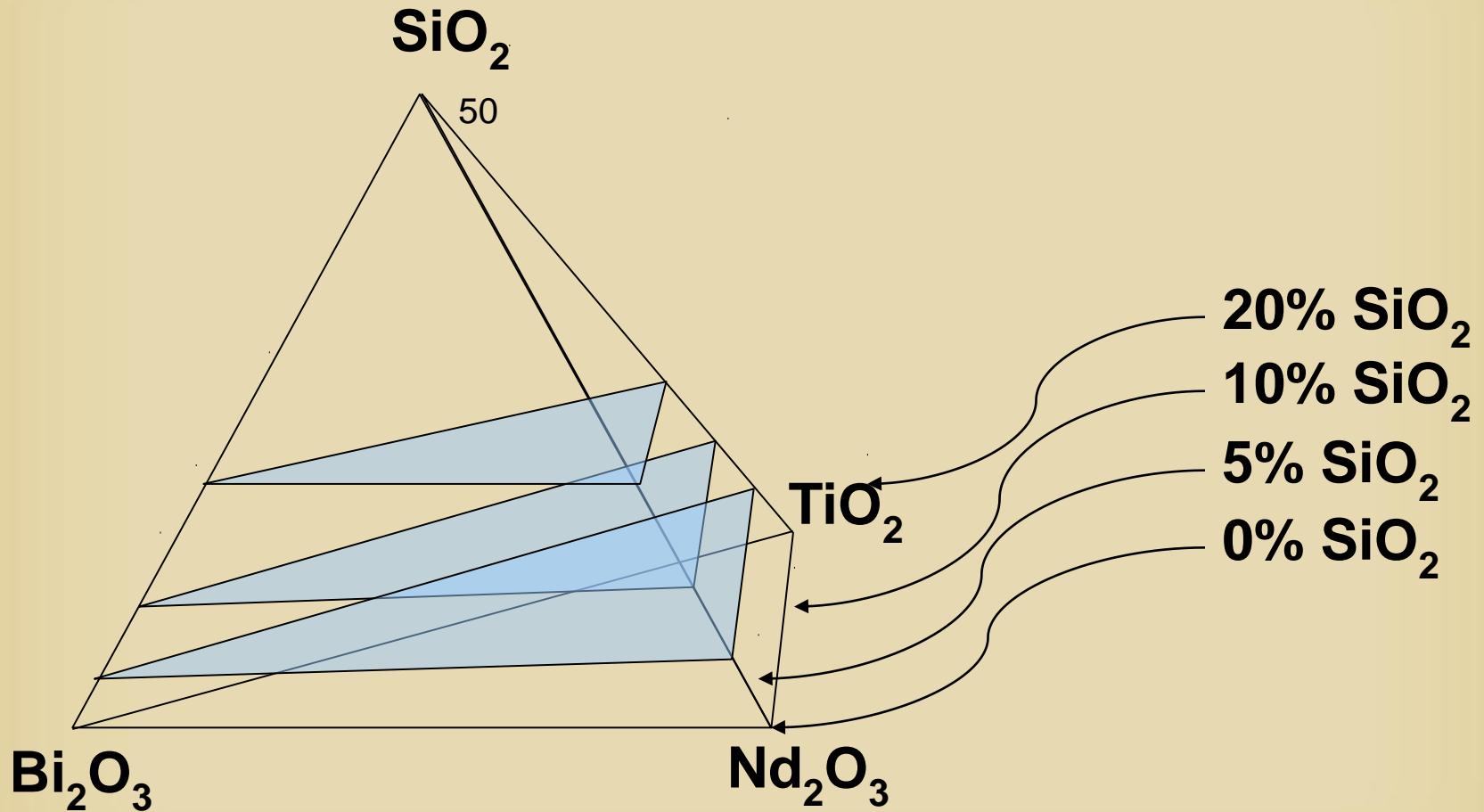
Experimental

The samples are synthesized by melt quenching method at fast cooling at room temperature, performed by pouring of the melts between two cooper plates. The melting is made in alumina crucibles at 1250 and 1500°C depending of compositions.

The phase formation has been studied through x-ray diffraction analysis (XRD - TUR M62, Cu-K α radiation).

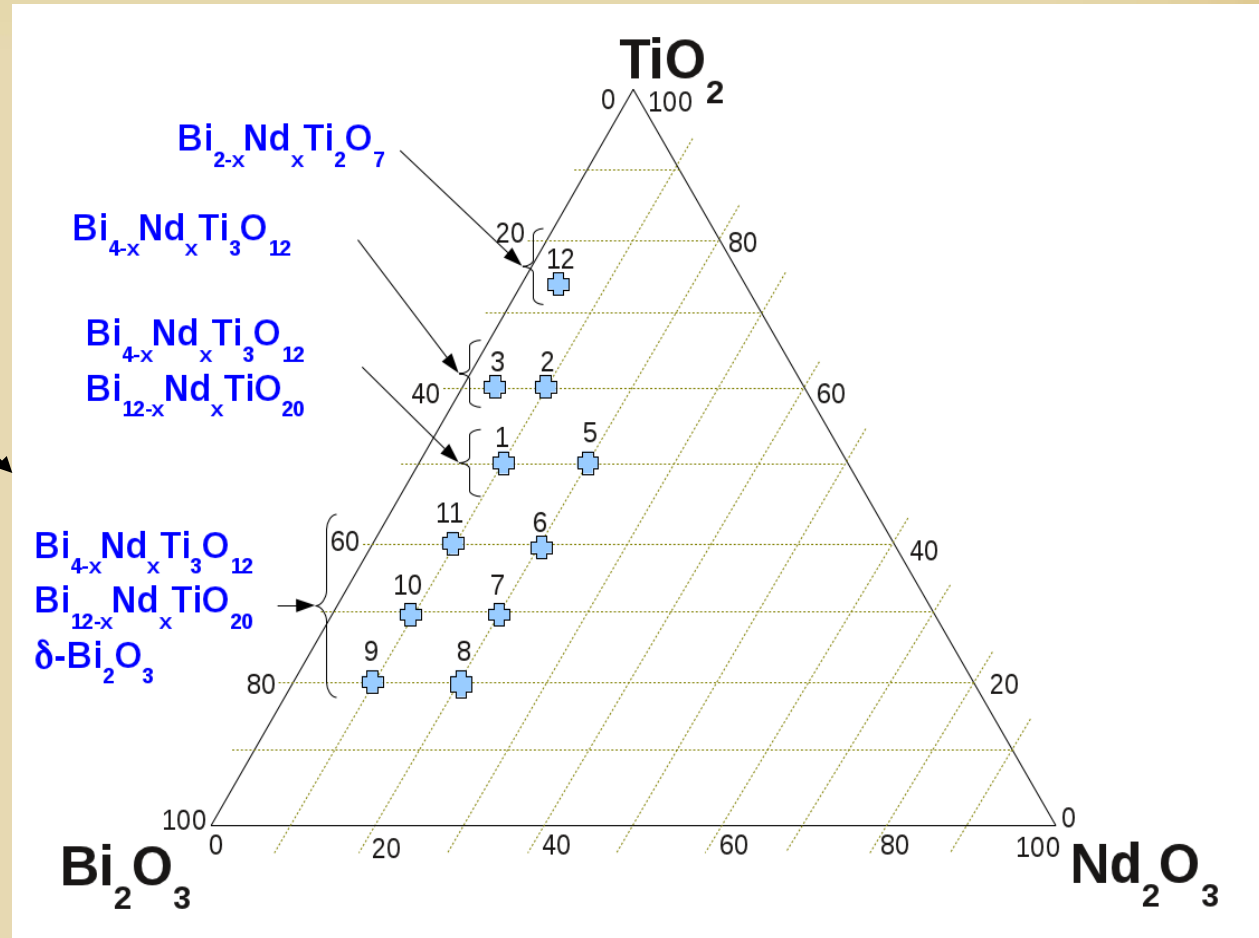
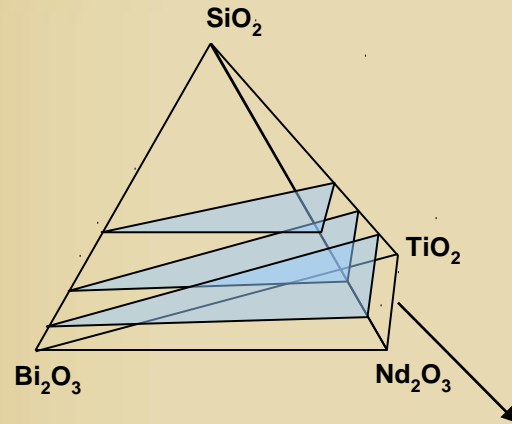
Measurements of the electrical conductivity, capacitance and dielectric losses of selected samples are performed by DC resistible bridge and digital capacity meter E8-4 using two-terminal method and a suitable sample holder with graphite electrodes.

Results



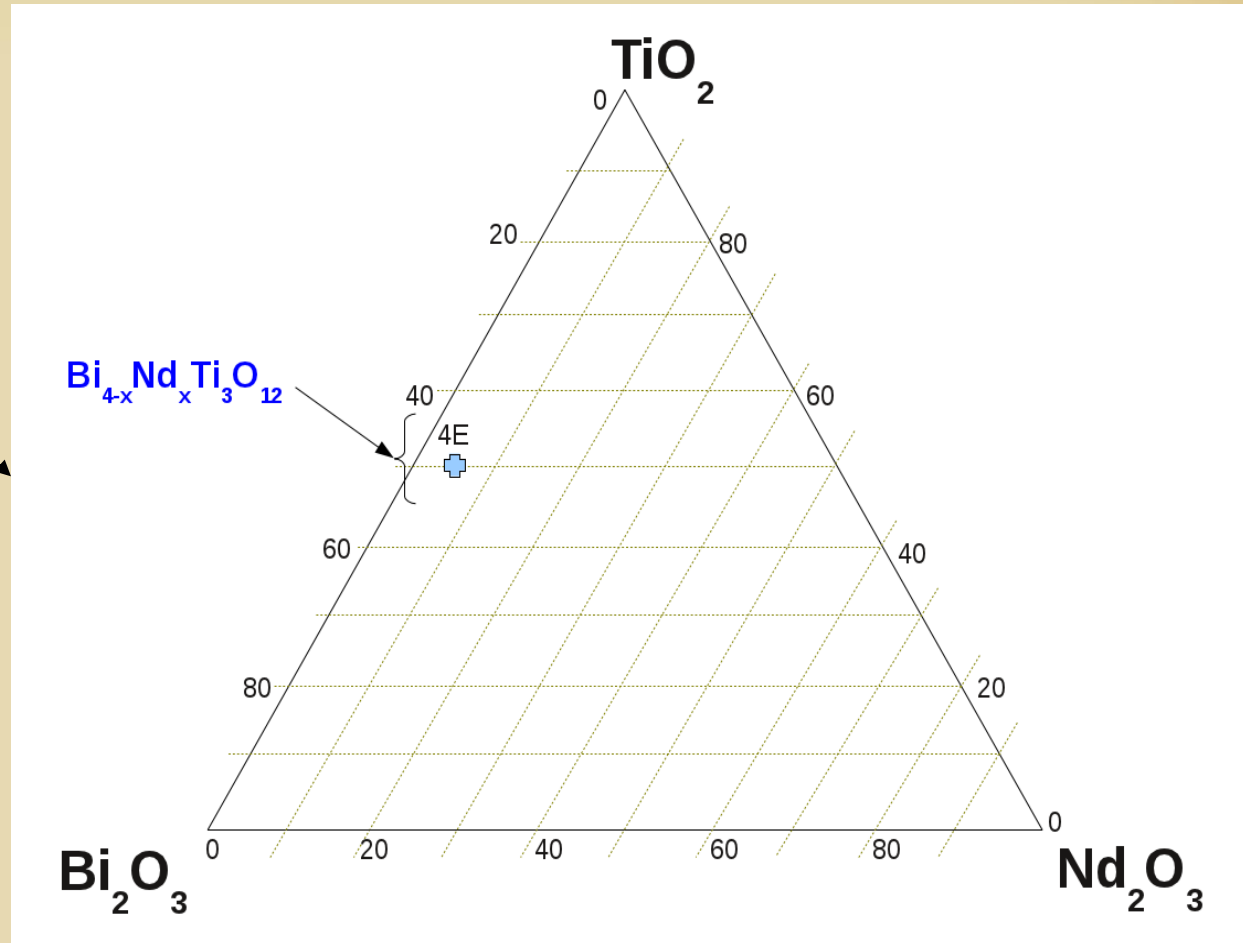
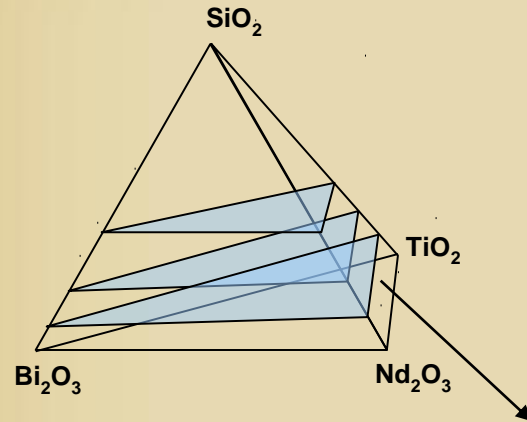
Results

0% SiO₂



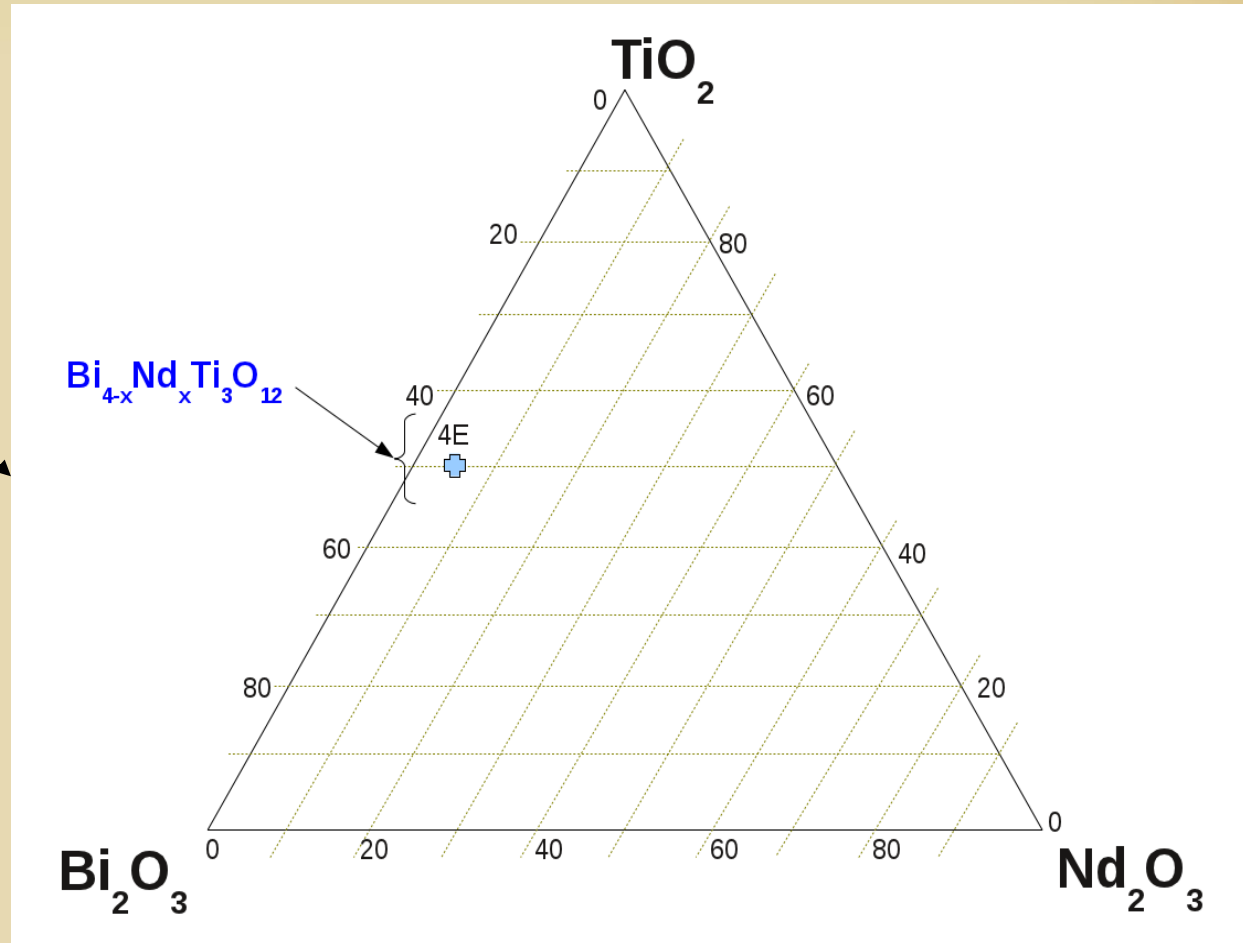
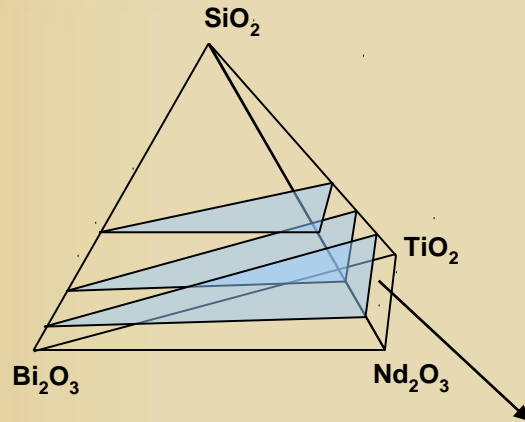
Results

5% SiO₂



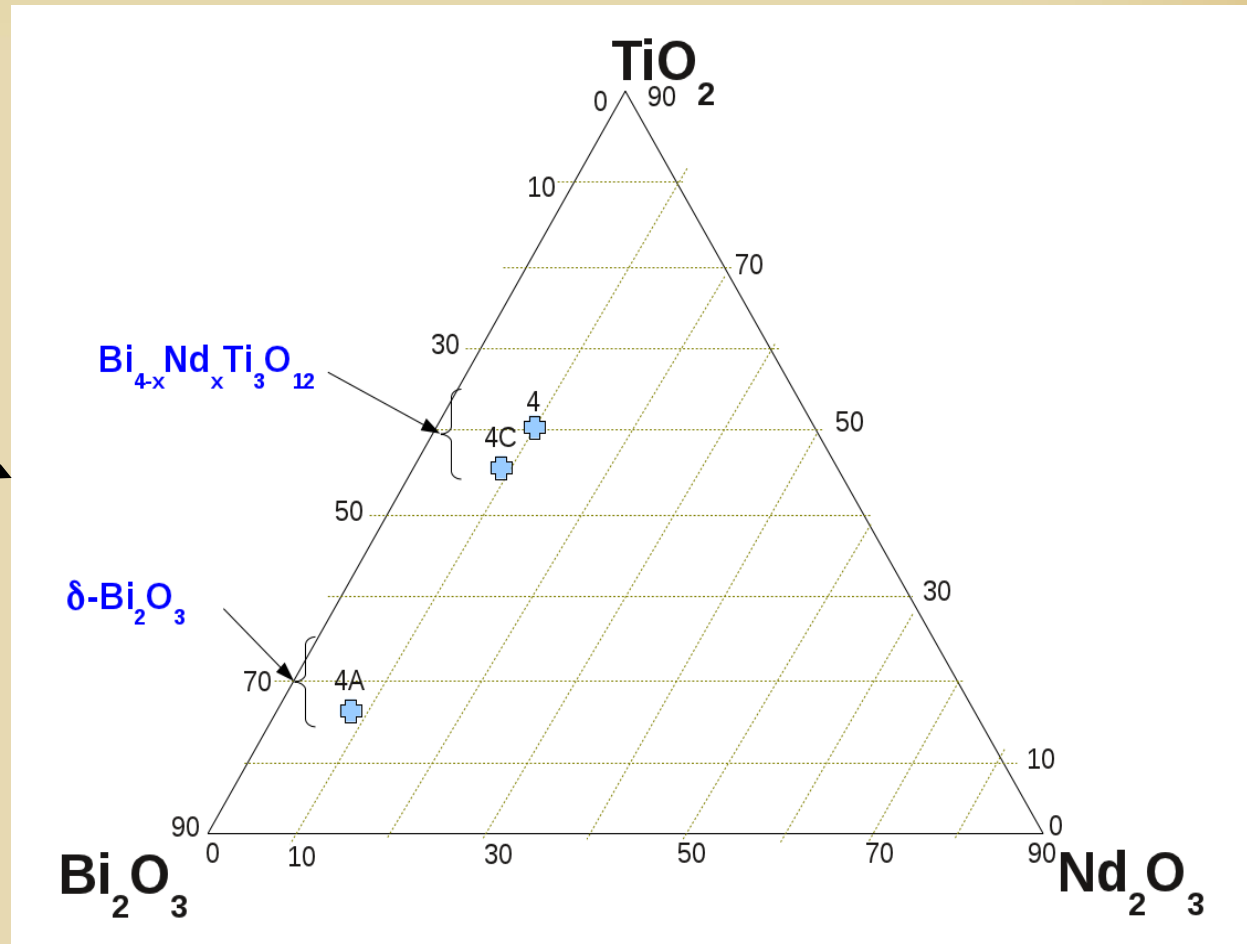
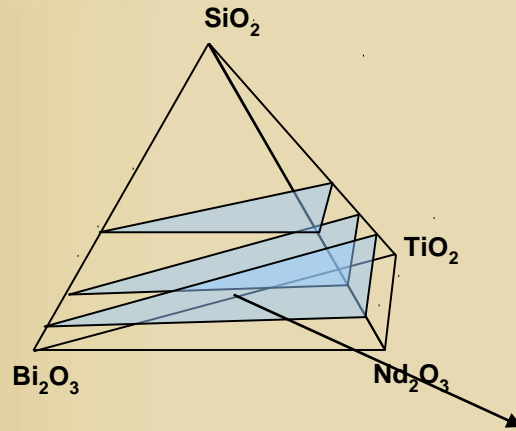
Results

5% SiO₂



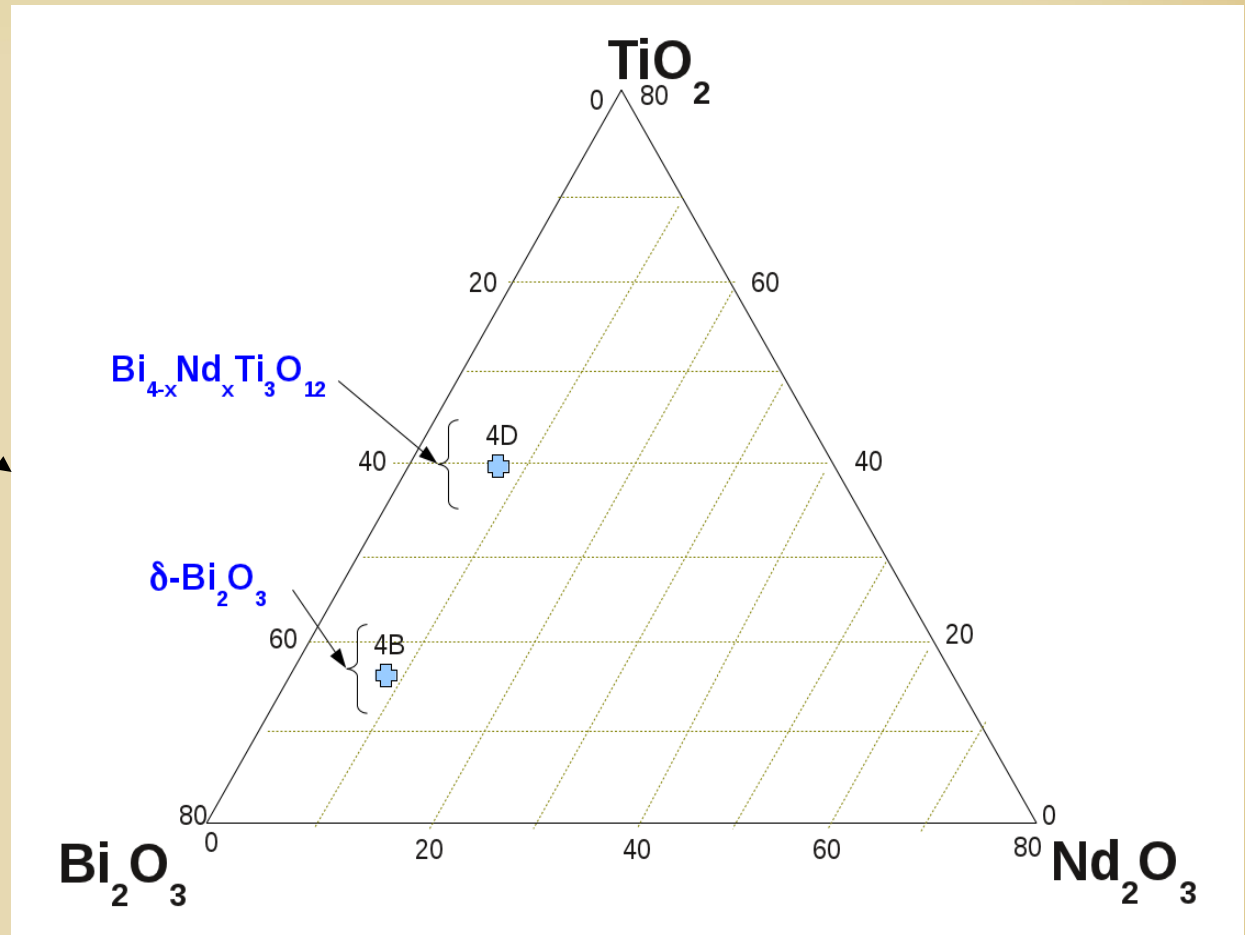
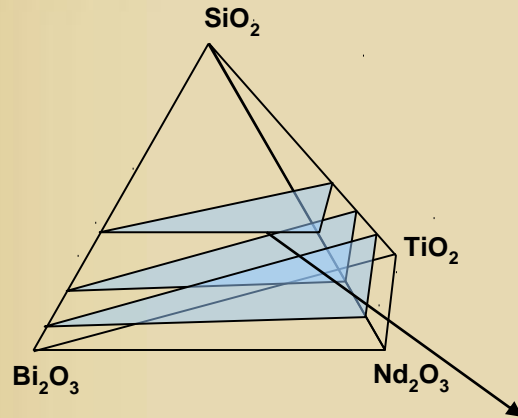
Results

10% SiO₂



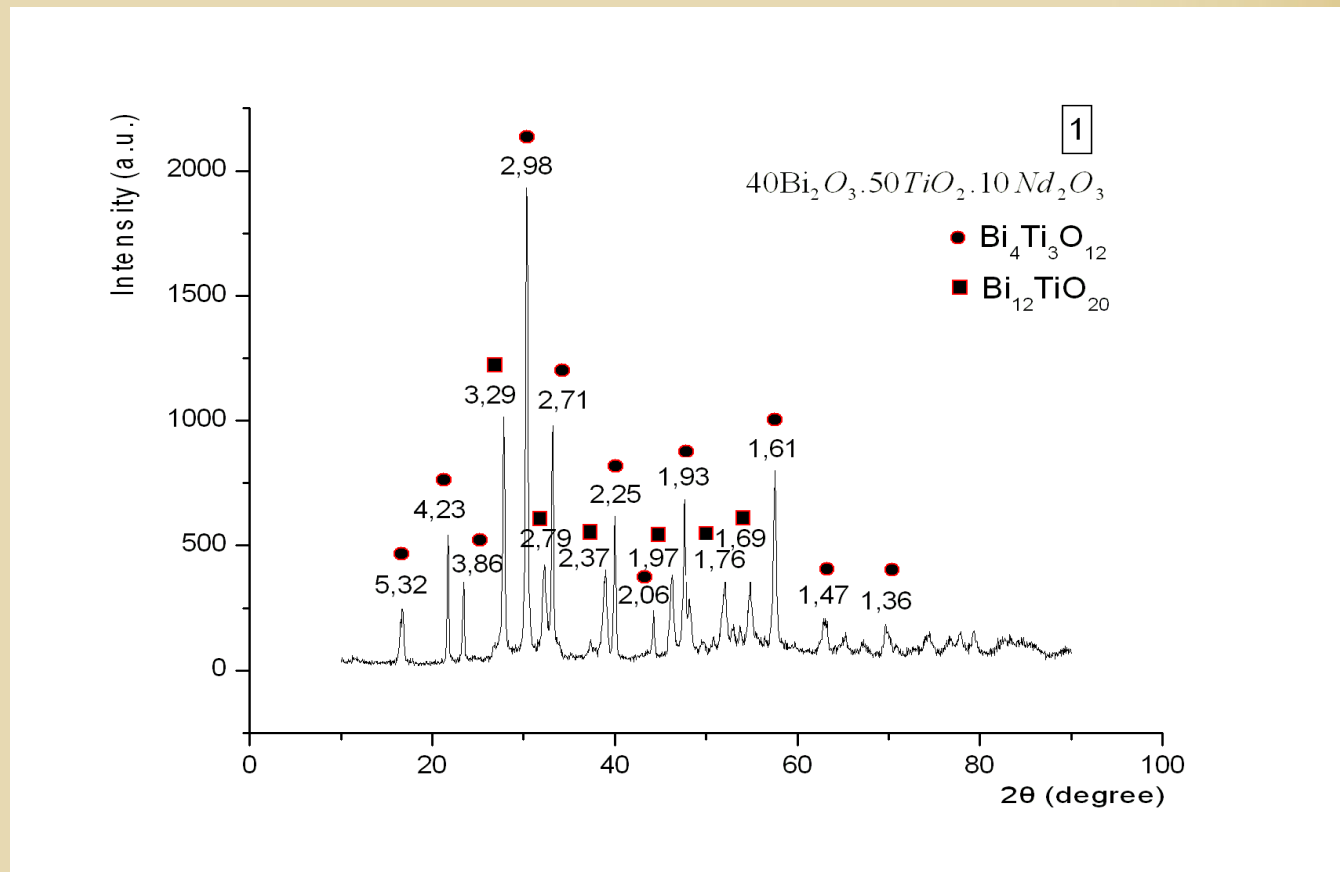
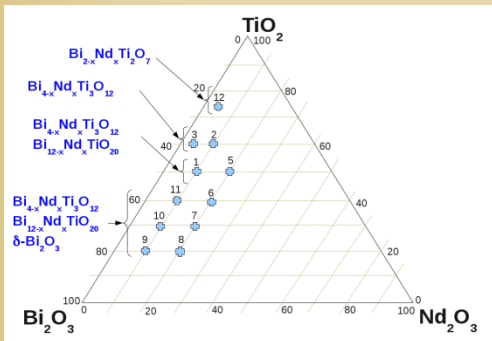
Results

20% SiO₂



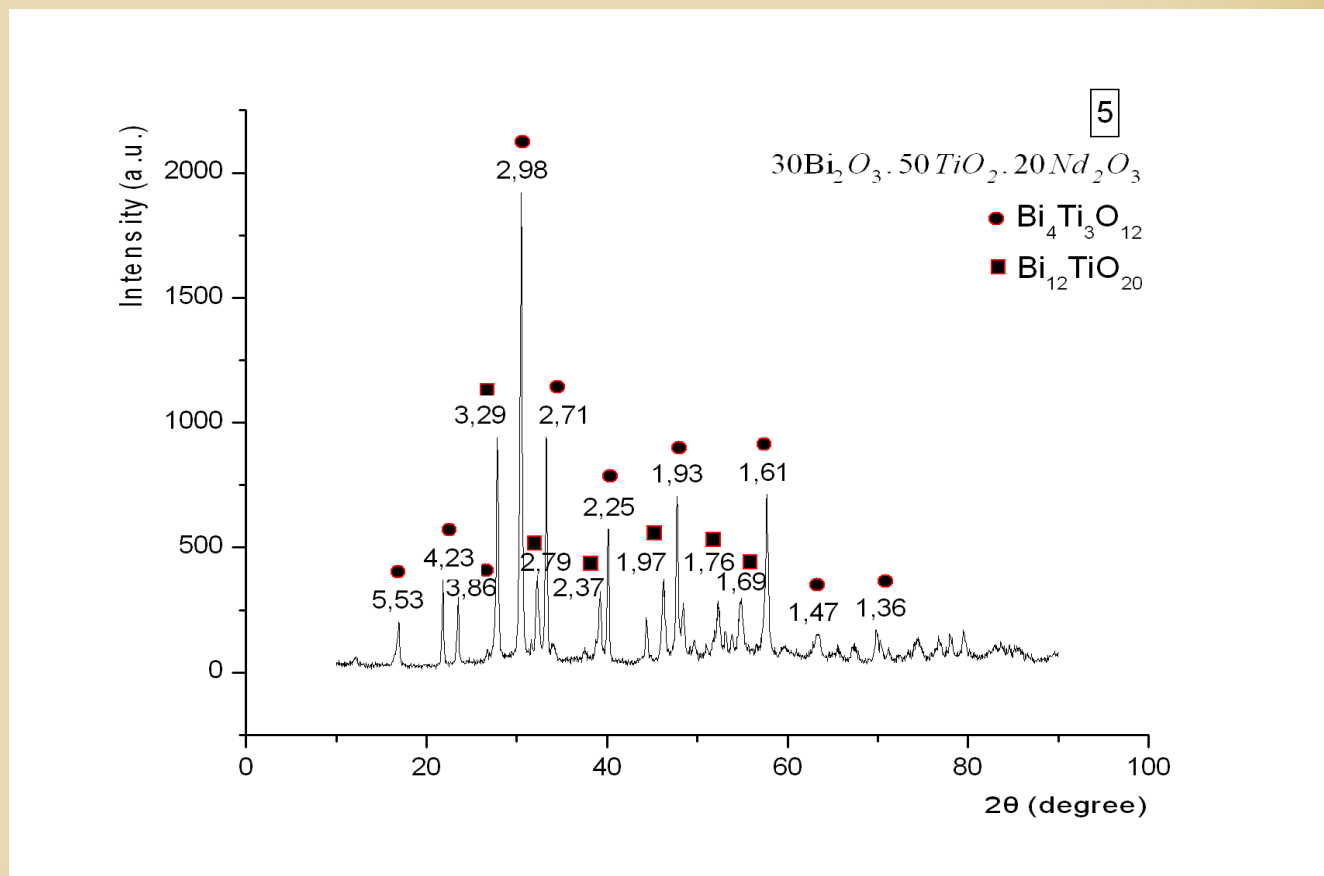
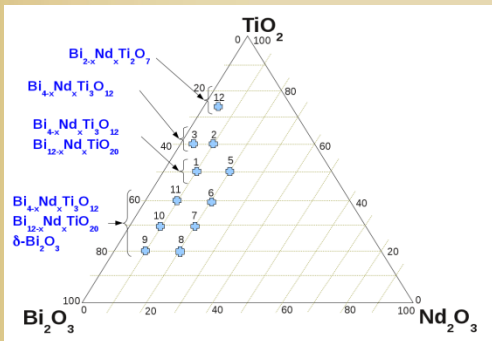
Results

0% SiO₂



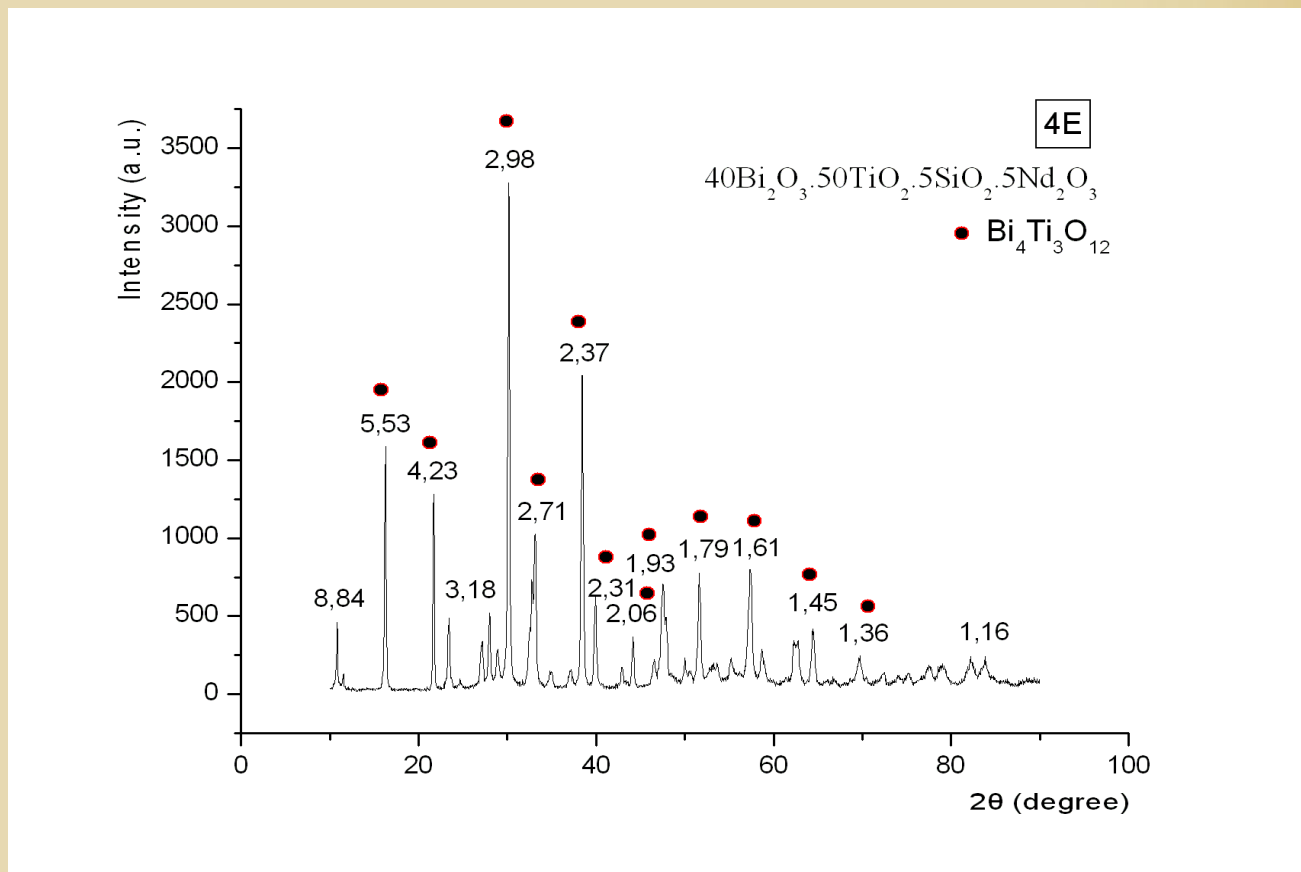
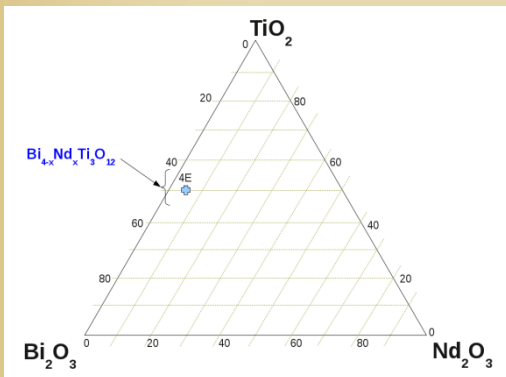
Results

0% SiO₂



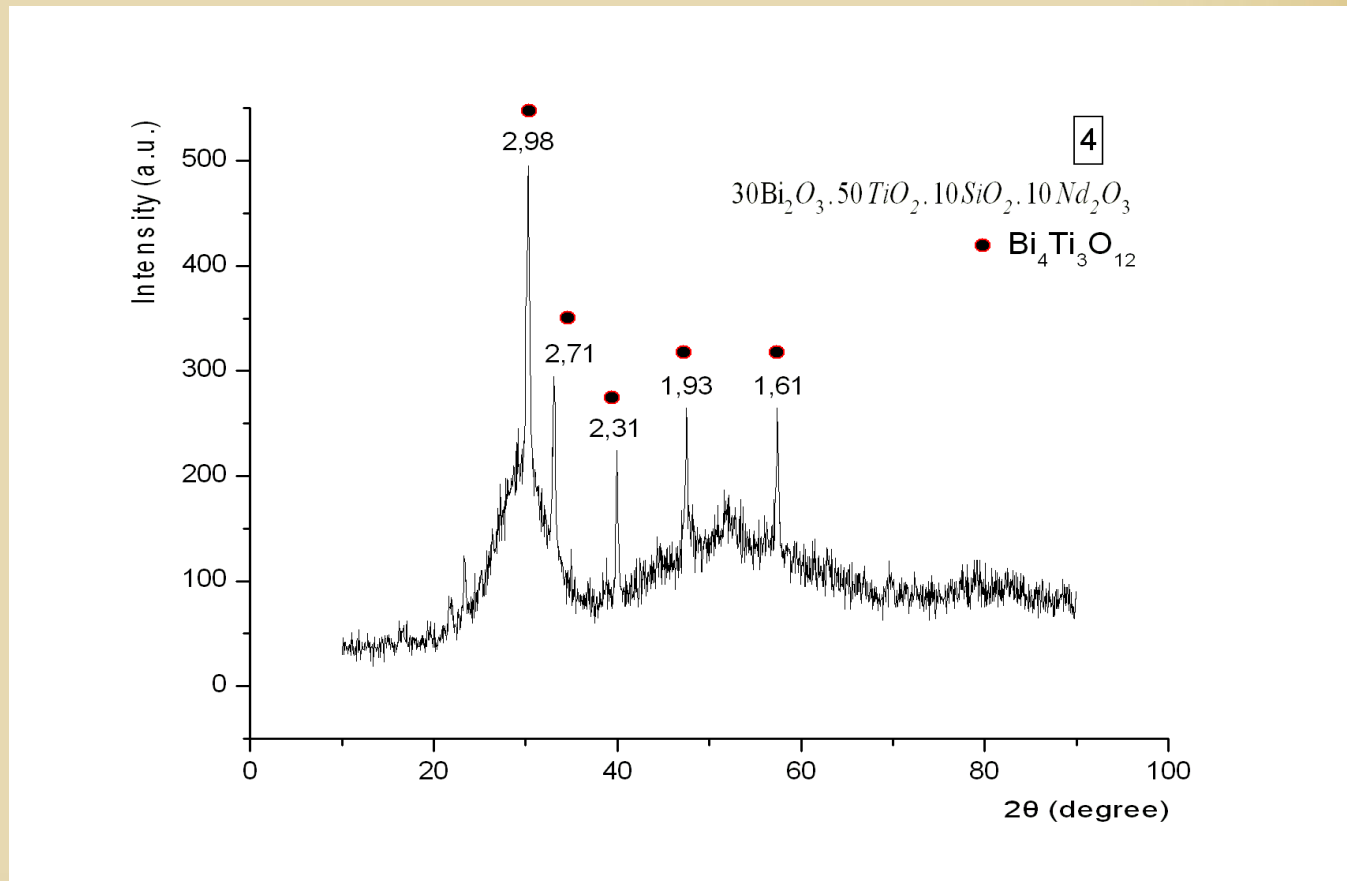
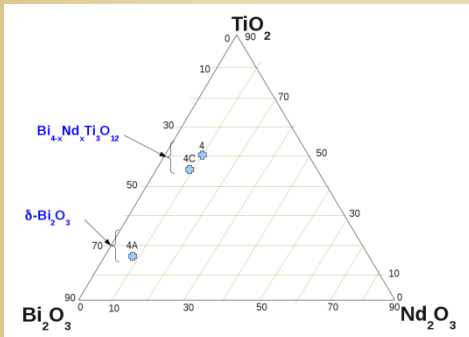
Results

5% SiO₂



Results

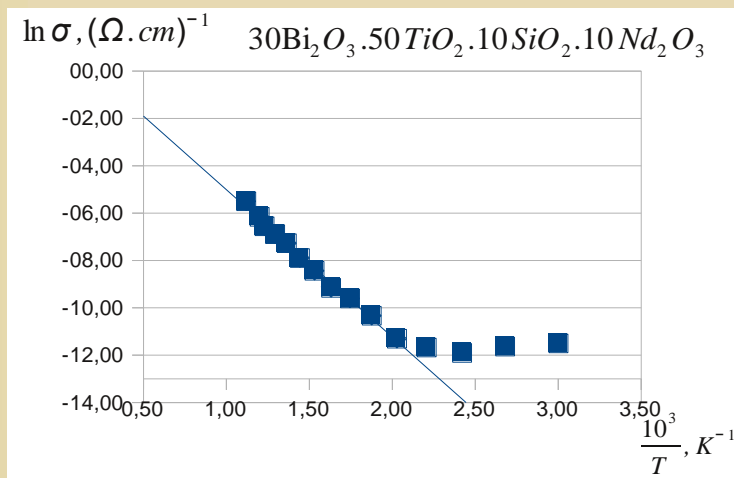
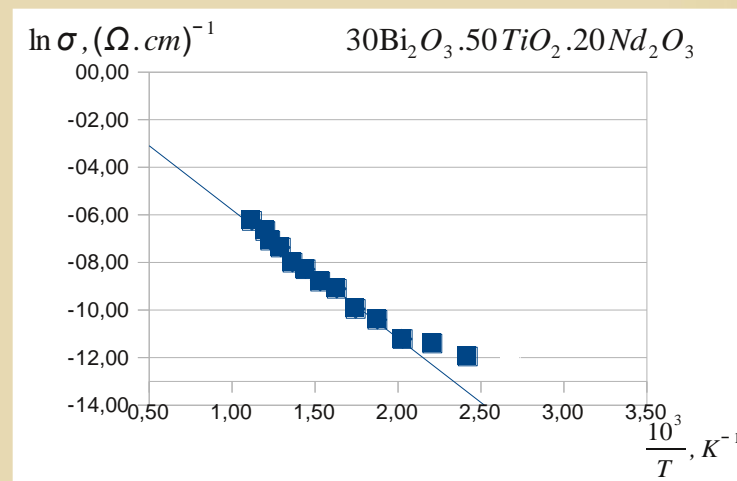
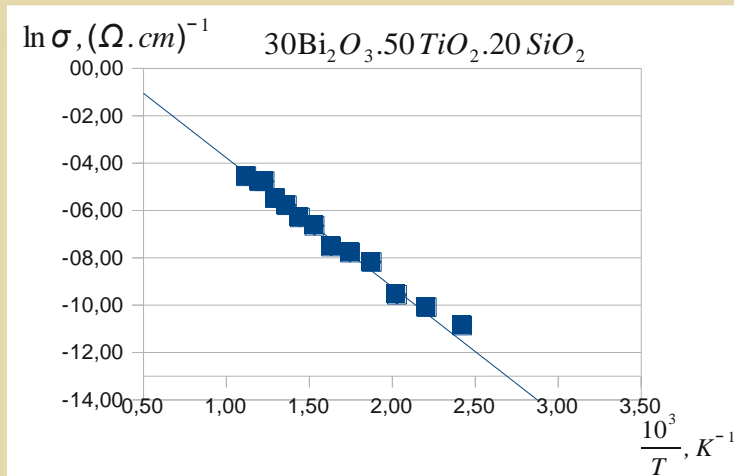
10% SiO₂



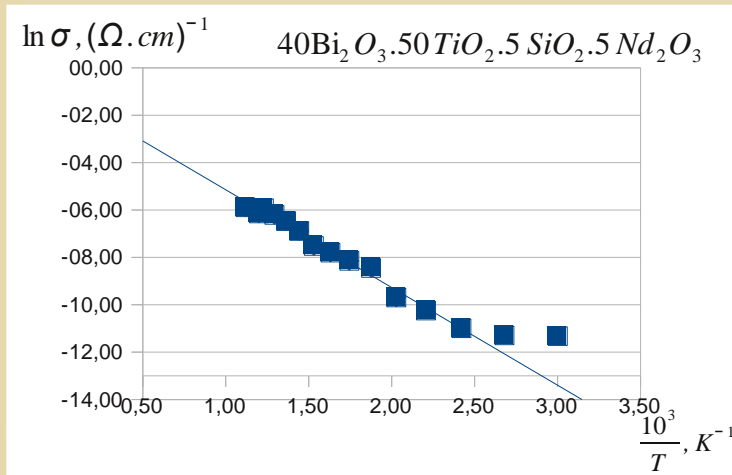
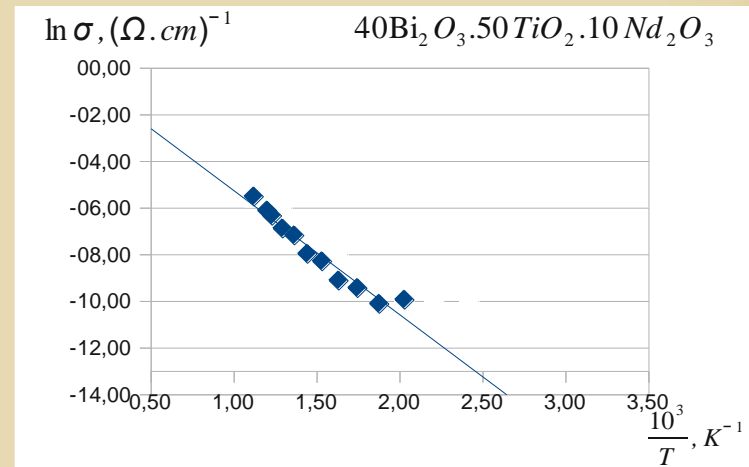
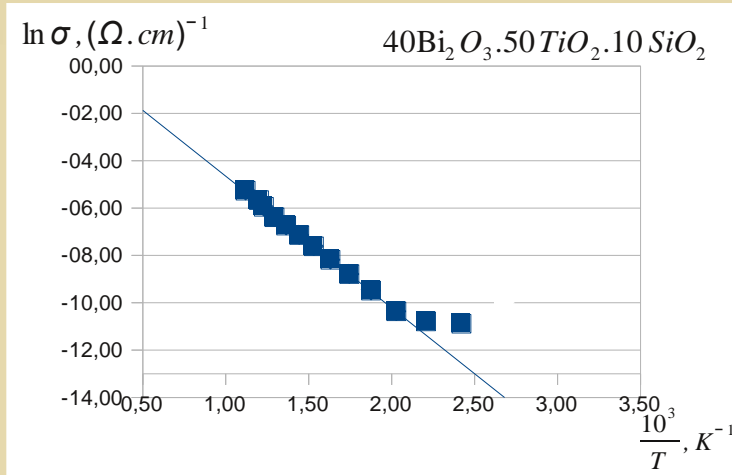
Results

Sample	Starting composition (mol %)				Identified phases XRD
	Bi ₂ O ₃	TiO ₂	Nd ₂ O ₃	SiO ₂	
1	40	50	10	--	Bi4, Bi12
2	25	65	10	--	Bi4
3	35	60	5	--	Bi4
4	30	50	10	10	Bi4
5	30	50	20	--	Bi4, Bi12
6	40	40	20	--	Bi4, Bi12, δ
7	50	30	20	--	Bi4, Bi12, δ
8	60	20	20	--	Bi4, Bi12, δ
9	70	20	10	--	Bi4, Bi12, δ
10	60	30	10	--	Bi4, Bi12, δ
11	50	40	10	--	Bi4, Bi12, δ
12	21	72	7	--	P
4A	63	18	10	9	δ
4B	56	16	20	8	δ
4C	36	45	10	9	Bi4
4D	32	40	20	8	Bi4
4E	40	50	5	5	Bi4

Results



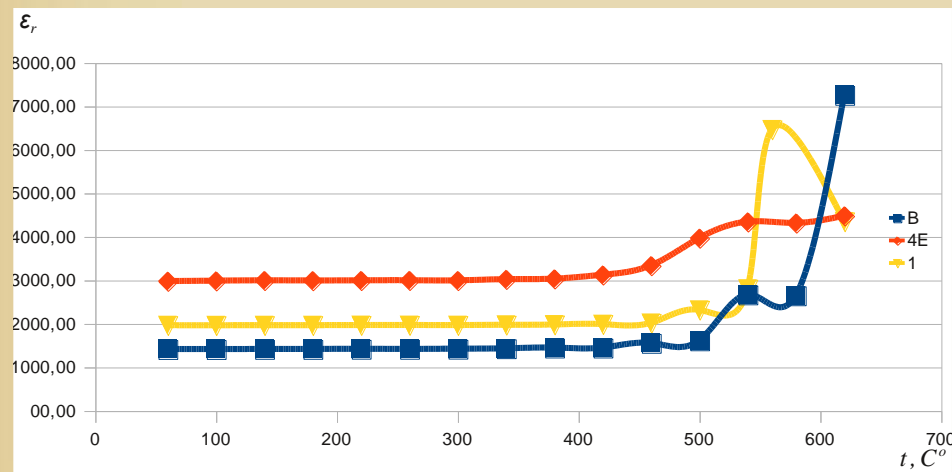
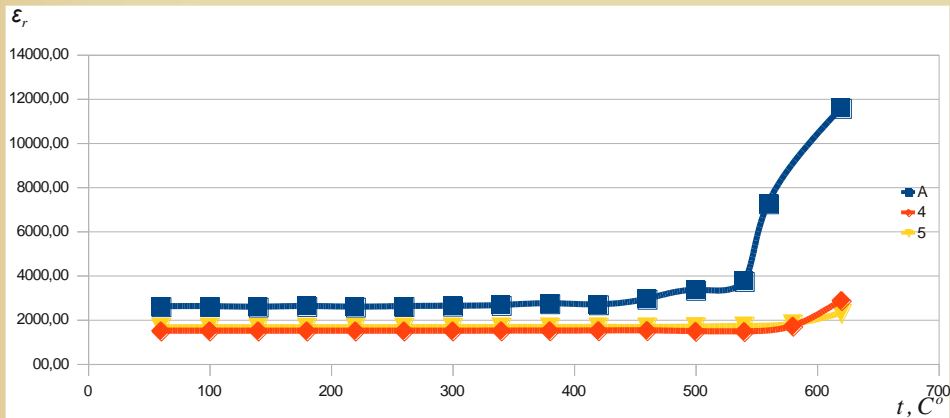
Results



Results

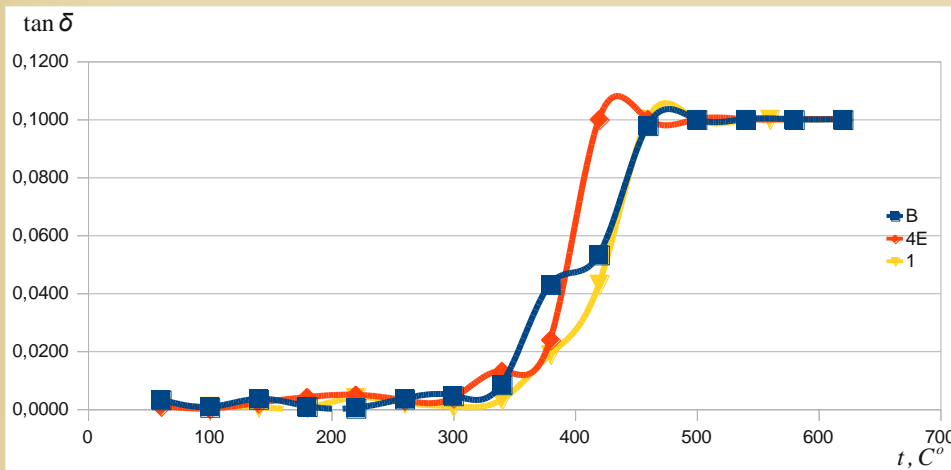
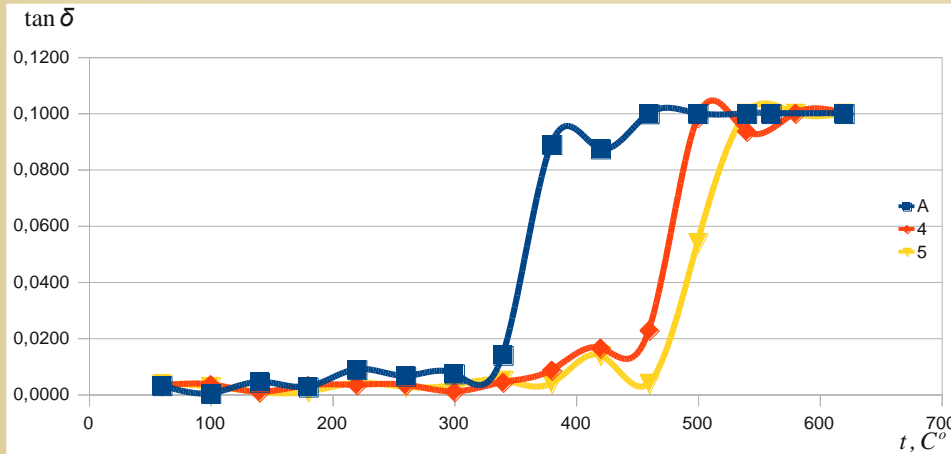
	Sample	Visual observation	Method of cooling	d, 10 ⁻³ m	σ , 10 ⁻⁷ (Ω.cm) ⁻¹	ΔE eV
A	30Bi₂O₃.50TiO₂.20SiO₂		T_m=1400 °C		33,10	1,21
		Black with milky regions	Fast Cooling	1,59		
4	30Bi₂O₃.50TiO₂.10SiO₂.10Nd₂O₃		T_m=1450 °C		1,29	1,38
		Dark silver	Fast Cooling	0,67		
5	30Bi₂O₃.50TiO₂.20Nd₂O₃		T_m=1500 °C		0,42	1,19
		Milk silver with yellow additives	Fast Cooling	0,75		
B	40Bi₂O₃.50TiO₂.10SiO₂		T_m=1260 °C		7,09	1,23
		Black with milky regions	Fast Cooling	0,63		
4E	40Bi₂O₃.50TiO₂.5SiO₂.5Nd₂O₃		T_m=1450 °C		6,19	1,14
		Milk silver	Fast Cooling	1,37		
1	40Bi₂O₃.50TiO₂.10Nd₂O₃		T_m=1450 °C		4,63	1,18
		Dark yellow with silver additives	Fast Cooling	0,89		

Results



Sample	
A	$30\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 20\text{SiO}_2$
4	$30\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 10\text{SiO}_2 \cdot 10\text{Nd}_2\text{O}_3$
5	$30\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 20\text{Nd}_2\text{O}_3$
B	$40\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 10\text{SiO}_2$
4E	$40\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 5\text{SiO}_2 \cdot 5\text{Nd}_2\text{O}_3$
1	$40\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 10\text{Nd}_2\text{O}_3$

Results



Sample	
A	$30\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 20\text{SiO}_2$
4	$30\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 10\text{SiO}_2 \cdot 10\text{Nd}_2\text{O}_3$
5	$30\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 20\text{Nd}_2\text{O}_3$
B	$40\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 10\text{SiO}_2$
4E	$40\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 5\text{SiO}_2 \cdot 5\text{Nd}_2\text{O}_3$
1	$40\text{Bi}_2\text{O}_3 \cdot 50\text{TiO}_2 \cdot 10\text{Nd}_2\text{O}_3$

Conclusion

- 1. The investigation carried out confirms that depending on the condition of the melting of the super-cooled melt different poly-phase glass-ceramic materials with various microstructure could be obtained containing mainly the bismuth titanate phase in the system $\text{Bi}_2\text{O}_3\text{-TiO}_2\text{-SiO}_2\text{-Nd}_2\text{O}_3$.**
- 2. Addition of Nd_2O_3 in the samples leads to increase of the melting temperature and decrease of glass-formation tendency.**
- 3. It is established that all investigated samples are dielectric materials with conductivity between $10^{-9}\text{-}10^{-13}$ ($\Omega\text{ cm}$)⁻¹ at room temperature, dielectric permittivity near 1000 to 3000 and dielectric losses $\text{tag}\delta$ between 0,0002 – 0,1.**
- 4. Addition of SiO_2 in the samples leads to increasing of dielectric losses and conductivity.**



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Thanks for your attention

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